EXHIBIT S

EX-HIB1023- USP 7,709,900 - OmniVision Technologies, Inc. QV8858 (Pixel)

1. A semiconductor device, comprising:

(A) an element isolation region formed on a semiconductor substrate;

(B1) a first active region which comprises the semiconductor substrate surrounded by the element isolation region;

(C1) a first gate conductor film which is formed across the first active region and the element isolation region, and has *substantially constant dimension* in a gate length direction;

(D) an interlayer insulating film formed on the first gate conductor film; and

(E1) a first gate contact which passes through the interlayer insulating film, and is connected to the first gate conductor wherein

(E1) the first gate contact has a dimension in the gate length direction larger than **(C1) the first gate conductor film**,
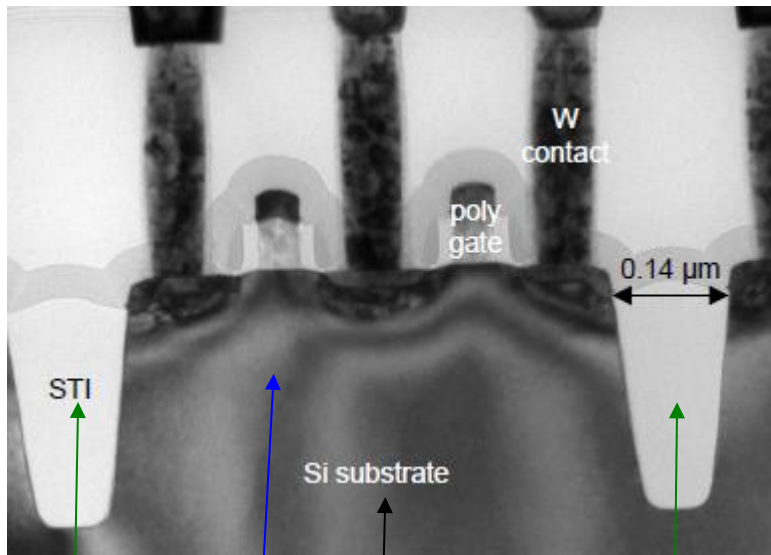
(E1) the first gate contact is connected to a part located on **(C1) the first gate conductor film** and on **(A) the element region**, and

(E1) the first gate contact is not connected to a part located on **(C1) the first gate conductor film** and on **(B1) the first region**.

EXHIBIT 19 - USP 7,709,900 - OmniVision Technologies, Inc. OV8858 (Pixel)

Claim 1

A semiconductor device, comprising: **(A) an element isolation region** formed on a semiconductor substrate;
(B1) a first active region which comprises the semiconductor substrate surrounded by the element isolation region;
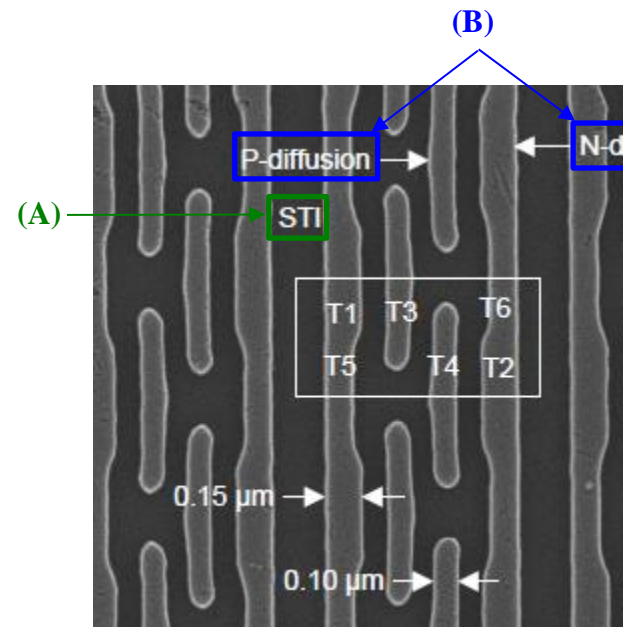
(Cross section : gate length direction)

(Plane : diffusion level)

(B)

W contact

poly gate

0.14 μm

STI

Si substrate

(A)   **(B)**   **(A)**

a semiconductor substrate

(A) — STI

P-diffusion   N-d
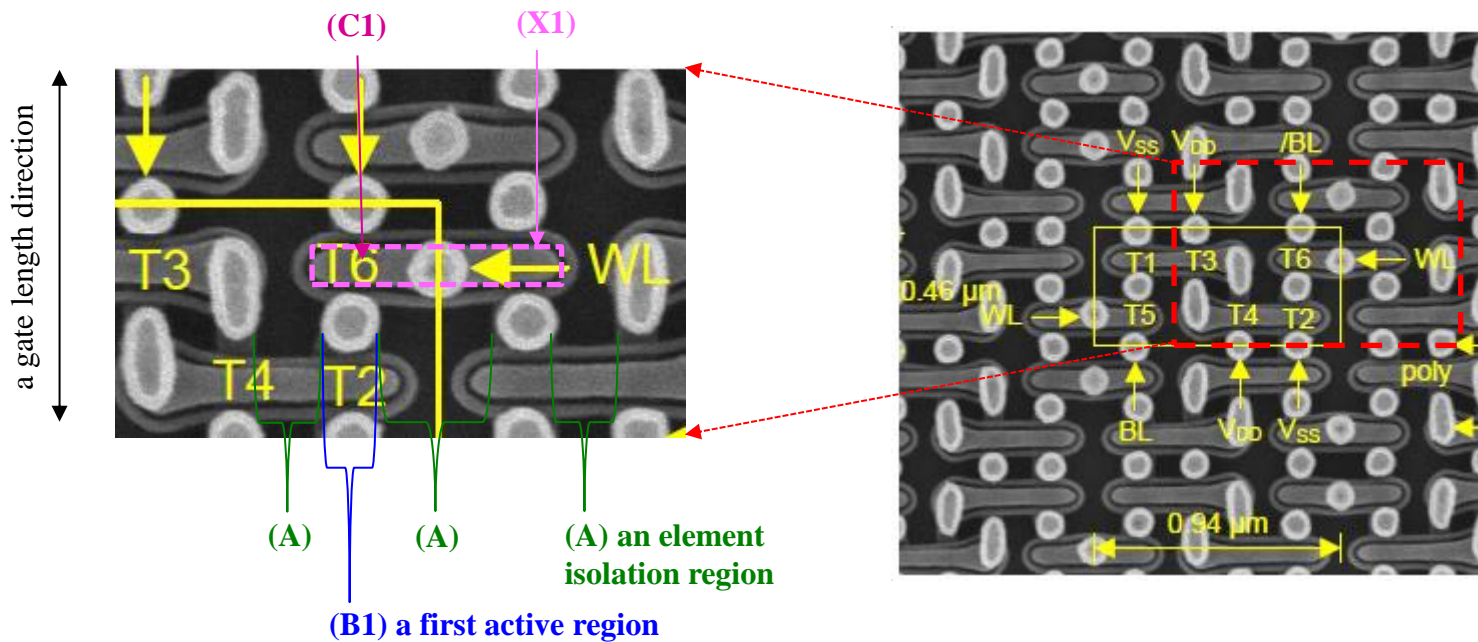
T1 T3   T6
T5   T4 T2

0.15 μm

0.10 μm

Claim 1

(C1) a first gate conductor film which is formed across the first active region and the element isolation region, and has **substantially constant dimension** in a gate length direction;
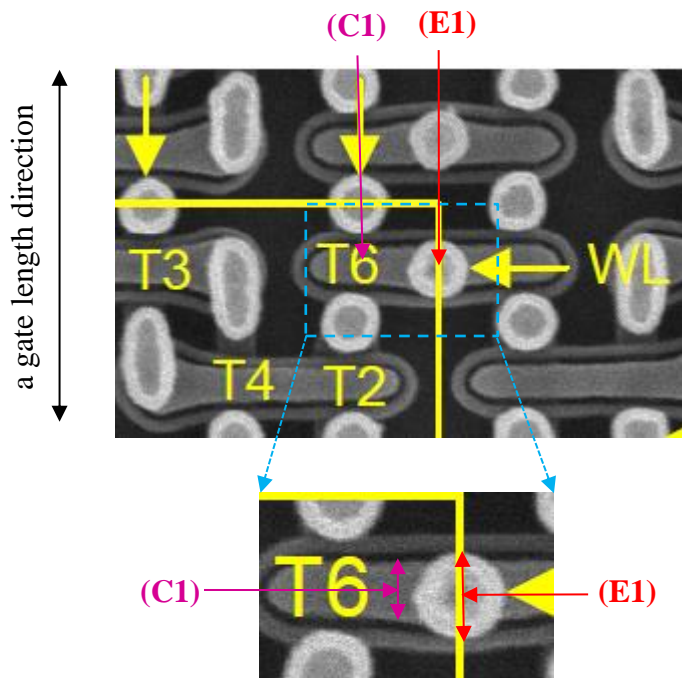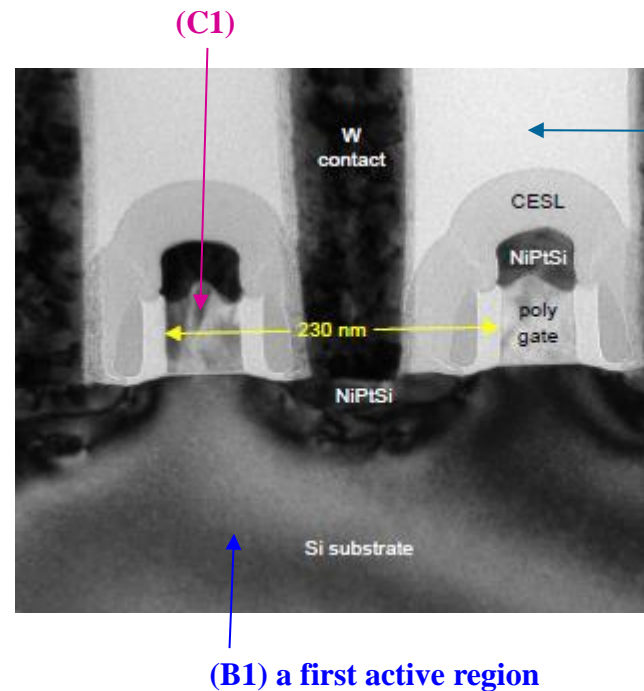
(Plane : gate level)

(A) an element isolation region

(B1) a first active region

Claim 1

(D) an interlayer insulating film formed on the first gate conductor film; and **(E1) a first gate contact** which passes th[...]
interlayer insulating film, and is connected to the first gate conductor film , wherein **(E1) the first gate contact** has a di[...]
gate length direction larger than **(C1) the first gate conductor film**,

(Plane : gate level)   (Cross section : gate length direction)

(C1)   **(E1)**   **(C1)**

(B1) a first active region

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